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30 V, single N-channel Trench MOSFET 3 August 2012

**Product data sheet** 

# 1. Product profile

## 1.1 General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

## **1.2 Features and benefits**

- Low R<sub>DSon</sub>
- Very fast switching
- Trench MOSFET technology

## 1.3 Applications

- Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

## 1.4 Quick reference data

| Table 1. Qu       | iick reference data              |   |     |     |     |     |      |
|-------------------|----------------------------------|---|-----|-----|-----|-----|------|
| Symbol            | Parameter                        | Conditions  |     | Min | Тур | Max | Unit |
| V <sub>DS</sub>   | drain-source voltage             | T <sub>amb</sub> = 25 °C  |     | -   | -   | 30  | V    |
| V <sub>GS</sub>   | gate-source voltage              | -   |     | -12 | -   | 12  | V    |
| I <sub>D</sub>    | drain current                    | $V_{GS}$ = 4.5 V; $T_{amb}$ = 25 °C; t ≤ 5 s                            | [1] | -   | -   | 1.2 | А    |
| Static charac     | teristics                        | 1   |     |     |     |     |      |
| R <sub>DSon</sub> | drain-source on-state resistance | V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 1.1 A; T <sub>j</sub> = 25 °C |     | -   | 185 | 250 | mΩ   |

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.





#### 30 V, single N-channel Trench MOSFET

# 2. Pinning information

| Table 2. | Pinning | information |                         |                       |
|----------|---------|-------------|-------------------------|-----------------------|
| Pin      | Symbol  | Description | Simplified outline      | Graphic symbol        |
| 1        | G       | gate        | 3                       | D                     |
| 2        | S       | source      |                         |                       |
| 3        | D       | drain       | 1 2<br>TO-236AB (SOT23) | G 4<br>S<br>017aaa253 |

# 3. Ordering information

| Table 3. Ordering information |          |  |         |  |  |
|-------------------------------|----------|--|---------|--|--|
| Type number                   | Package  |  |         |  |  |
|                               | Name     | Description                              | Version |  |  |
| PMV185XN                      | TO-236AB | plastic surface-mounted package; 3 leads | SOT23   |  |  |

# 4. Marking

| Table 4. Marking codes |              |
|------------------------|--------------|
| Type number            | Marking code |
|                        | [1]          |
| PMV185XN               | EH%          |

[1] % = placeholder for manufacturing site code

# 5. Limiting values

#### Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol           | Parameter               | Conditions  |     | Min | Мах  | Unit |
|------------------|-------------------------|---|-----|-----|------|------|
| V <sub>DS</sub>  | drain-source voltage    | T <sub>amb</sub> = 25 °C                              |     | -   | 30   | V    |
| V <sub>GS</sub>  | gate-source voltage     |   |     | -12 | 12   | V    |
| I <sub>D</sub>   | drain current           | $V_{GS}$ = 4.5 V; $T_{amb}$ = 25 °C; t ≤ 5 s          | [1] | -   | 1.2  | А    |
|                  |                         | $V_{GS}$ = 4.5 V; $T_{amb}$ = 25 °C                   | [1] | -   | 1.1  | А    |
|                  |                         | $V_{GS}$ = 4.5 V; $T_{amb}$ = 100 °C                  | [1] | -   | 0.7  | А    |
| I <sub>DM</sub>  | peak drain current      | $T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \ \mu s$ |     | -   | 4.4  | А    |
| P <sub>tot</sub> | total power dissipation | T <sub>amb</sub> = 25 °C                              | [2] | -   | 325  | mW   |
|                  |                         |   | [1] | -   | 455  | mW   |
|                  |                         | T <sub>sp</sub> = 25 °C                               |     | -   | 1275 | mW   |

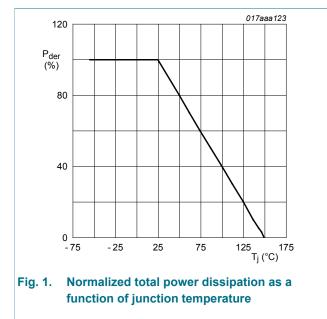
# **PMV185XN**

#### 30 V, single N-channel Trench MOSFET

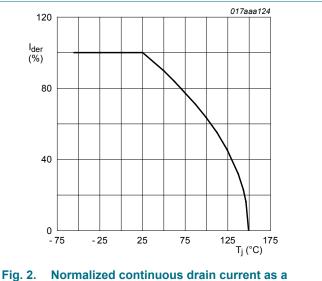
| Symbol             | Parameter            | Conditions               |     | Min | Мах | Unit |
|--------------------|----------------------|--------------------------|-----|-----|-----|------|
| Tj                 | junction temperature |                          |     | -55 | 150 | °C   |
| T <sub>amb</sub>   | ambient temperature  |                          |     | -55 | 150 | °C   |
| T <sub>stg</sub>   | storage temperature  |                          |     | -65 | 150 | °C   |
| Source-drain diode |                      |                          |     |     |     |      |
| l <sub>S</sub>     | source current       | T <sub>amb</sub> = 25 °C | [1] | -   | 0.7 | А    |

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.

[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



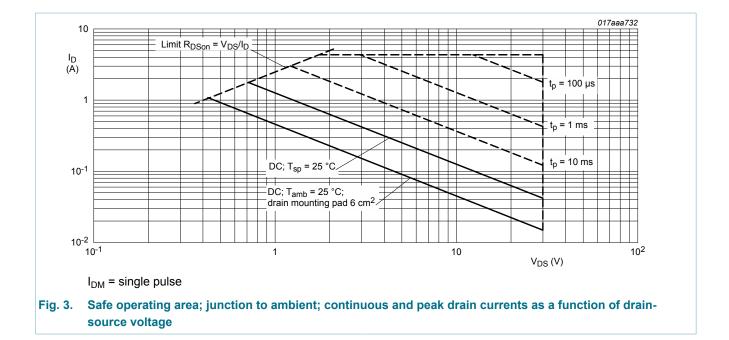
$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$





$$I_{der} = \frac{I_D}{I_{D(25^\circ C)}} \times 100 \%$$

#### 30 V, single N-channel Trench MOSFET



# 6. Thermal characteristics

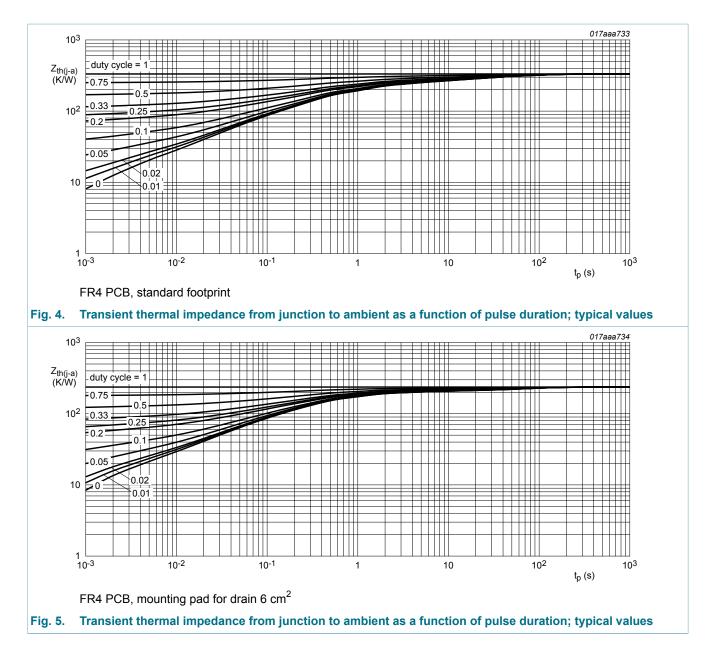
| Table 6. 1   | Thermal characteristics                                |                      |     |     |     |     |      |
|--|--|----------------------|-----|-----|-----|-----|------|
| Symbol   | Parameter  | Conditions           |     | Min | Тур | Max | Unit |
| R <sub>th(j-a)</sub> thermal resistance<br>from junction to<br>ambient |  | in free air          | [1] | -   | 333 | 385 | K/W  |
|  | -  |                      | [2] | -   | 240 | 275 | K/W  |
|  | amplent  | in free air; t ≤ 5 s | [2] | -   | 203 | 235 | K/W  |
| R <sub>th(j-sp)</sub>  | thermal resistance<br>from junction to solder<br>point |                      |     | -   | 85  | 100 | K/W  |

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.

# **PMV185XN**

#### 30 V, single N-channel Trench MOSFET



# 7. Characteristics

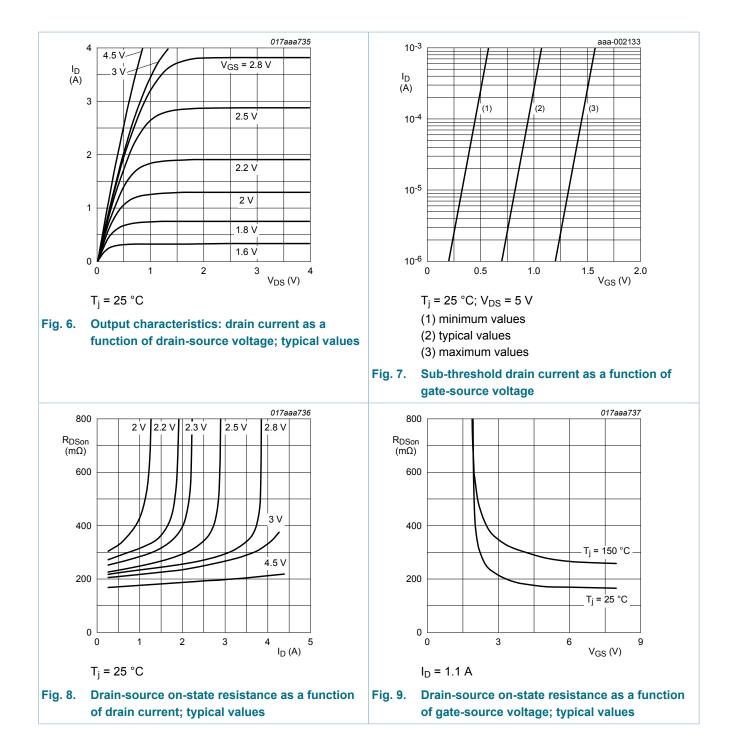
| Table 7. Ch            | naracteristics                    |   |  |     |     |               |                    |
|------------------------|-----------------------------------|---|--|-----|-----|---------------|--------------------|
| Symbol                 | Parameter                         | Conditions  |  | Min | Тур | Мах           | Unit               |
| Static characteristics |                                   |   |  |     |     |               |                    |
| V <sub>(BR)DSS</sub>   | drain-source<br>breakdown voltage | $I_D$ = 250 µA; $V_{GS}$ = 0 V; $T_j$ = 25 °C                                       |  | 30  | -   | -             | V                  |
| V <sub>GSth</sub>      | gate-source threshold voltage     | I <sub>D</sub> = 250 μA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 25 °C |  | 0.5 | 1   | 1.5           | V                  |
| I <sub>DSS</sub>       | drain leakage current             | $V_{DS}$ = 30 V; $V_{GS}$ = 0 V; $T_{amb}$ = 25 °C                                  |  | -   | -   | 1             | μA                 |
|                        |                                   | $V_{DS}$ = 30 V; $V_{GS}$ = 0 V; $T_{amb}$ = 150 °C                                 |  | -   | -   | 10            | μA                 |
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# **PMV185XN**

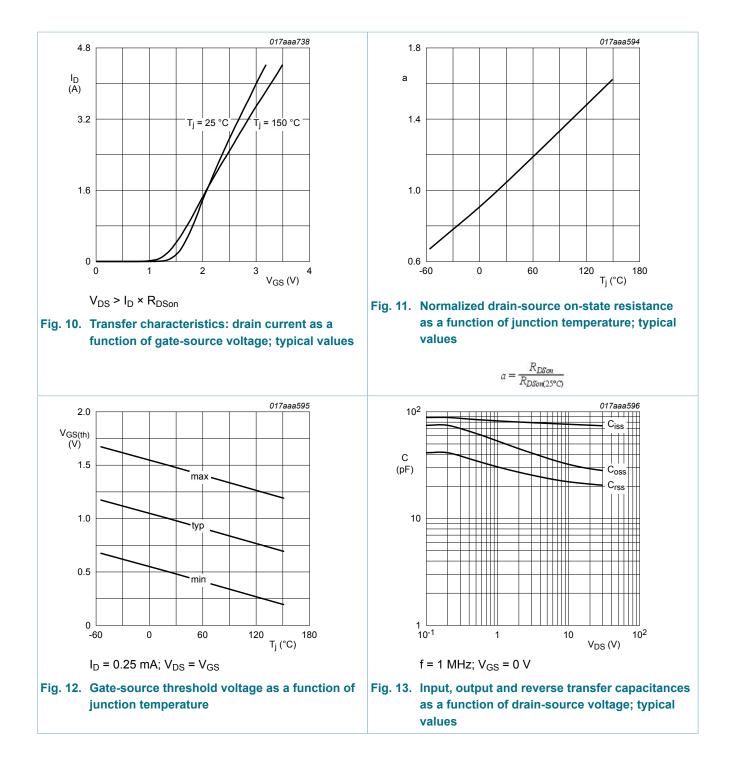
## 30 V, single N-channel Trench MOSFET

| Symbol              | Parameter                    | Conditions   | Min | Тур  | Max | Unit |
|---------------------|------------------------------|--|-----|------|-----|------|
| I <sub>GSS</sub>    | gate leakage current         | $V_{GS}$ = 12 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C                           | -   | -    | 100 | nA   |
|                     |                              | $V_{GS}$ = -12 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C                          | -   | -    | 100 | nA   |
| R <sub>DSon</sub>   | drain-source on-state        | V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 1.1 A; T <sub>j</sub> = 25 °C  | -   | 185  | 250 | mΩ   |
|                     | resistance                   | V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 1.1 A; T <sub>j</sub> = 150 °C | -   | 300  | 400 | mΩ   |
|                     |                              | $V_{GS}$ = 2.5 V; I <sub>D</sub> = 0.25 A; T <sub>j</sub> = 25 °C        | -   | 255  | 365 | mΩ   |
| 9 <sub>fs</sub>     | forward<br>transconductance  | V <sub>DS</sub> = 10 V; I <sub>D</sub> = 1.1 A; T <sub>j</sub> = 25 °C   | -   | 2.9  | -   | S    |
| Dynamic cl          | haracteristics               | · · · · · ·  | I   |      |     |      |
| Q <sub>G(tot)</sub> | total gate charge            | $V_{DS}$ = 15 V; I <sub>D</sub> = 1.1 A; V <sub>GS</sub> = 4.5 V;        | -   | 0.87 | 1.3 | nC   |
| Q <sub>GS</sub>     | gate-source charge           | T <sub>j</sub> = 25 °C   | -   | 0.17 | -   | nC   |
| Q <sub>GD</sub>     | gate-drain charge            | -  | -   | 0.24 | -   | nC   |
| C <sub>iss</sub>    | input capacitance            | V <sub>DS</sub> = 15 V; f = 1 MHz; V <sub>GS</sub> = 0 V;                | -   | 76   | -   | pF   |
| C <sub>oss</sub>    | output capacitance           | T <sub>j</sub> = 25 °C   | -   | 30   | -   | pF   |
| C <sub>rss</sub>    | reverse transfer capacitance | -  | -   | 22   | -   | pF   |
| t <sub>d(on)</sub>  | turn-on delay time           | $V_{DS}$ = 15 V; I <sub>D</sub> = 1.1 A; V <sub>GS</sub> = 4.5 V;        | -   | 7    | -   | ns   |
| t <sub>r</sub>      | rise time                    | R <sub>G(ext)</sub> = 6 Ω; T <sub>j</sub> = 25 °C                        | -   | 11   | -   | ns   |
| t <sub>d(off)</sub> | turn-off delay time          |  | -   | 16   | -   | ns   |
| t <sub>f</sub>      | fall time                    |  | -   | 7    | -   | ns   |
| Source-dra          | in diode                     |  | I   |      |     |      |
| V <sub>SD</sub>     | source-drain voltage         | I <sub>S</sub> = 0.7 A; V <sub>GS</sub> = 0 V; T <sub>i</sub> = 25 °C    | -   | 0.8  | 1.2 | V    |

#### 30 V, single N-channel Trench MOSFET



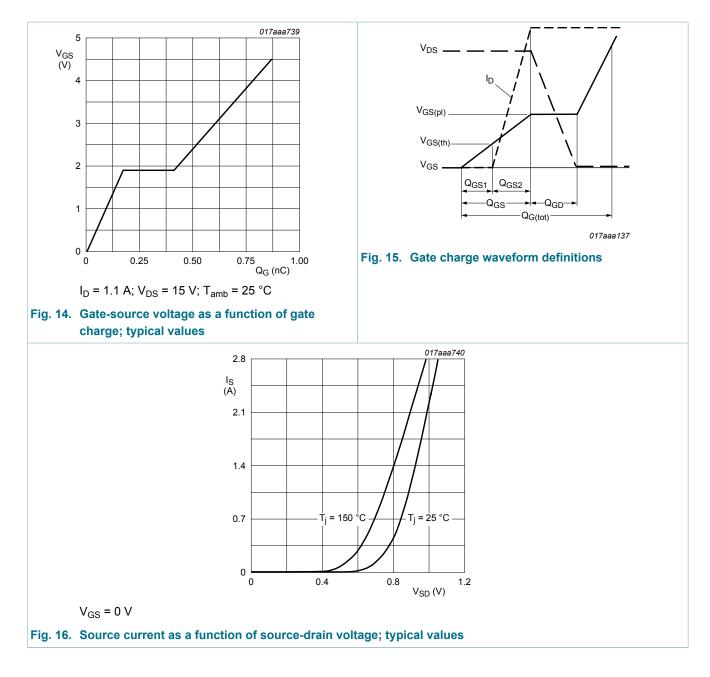
## 30 V, single N-channel Trench MOSFET



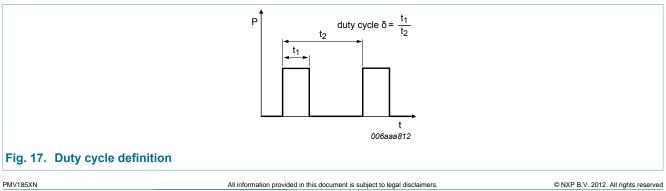
PMV185XN

# **PMV185XN**

#### 30 V, single N-channel Trench MOSFET

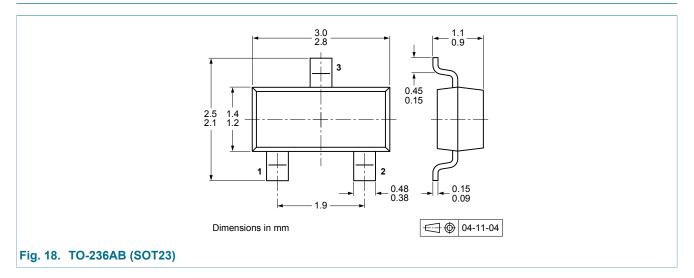


#### **Test information** 8.

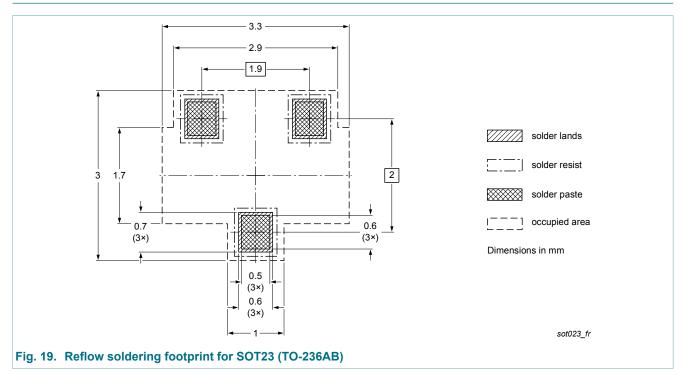


#### 30 V, single N-channel Trench MOSFET

# 9. Package outline

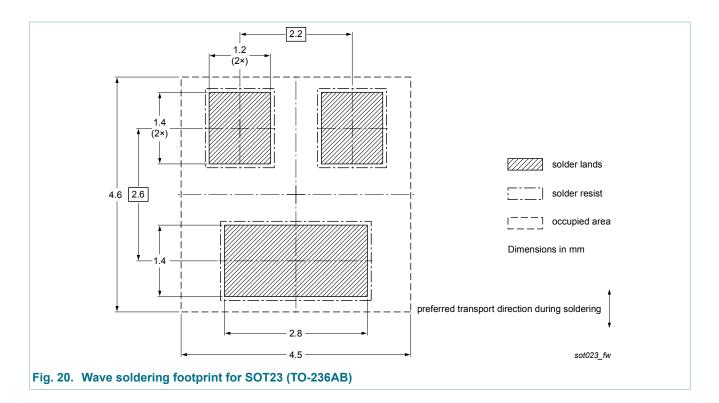


# 10. Soldering



# **PMV185XN**

#### 30 V, single N-channel Trench MOSFET



# 11. Revision history

## Table 8.Revision history

| Data sheet ID | Release date | Data sheet status  | Change notice | Supersedes |
|---------------|--------------|--------------------|---------------|------------|
| PMV185XN v.1  | 20120803     | Product data sheet | -             | -          |

#### 30 V, single N-channel Trench MOSFET

## 12. Legal information

#### 12.1 Data sheet status

| Document status [1][2]               | Product<br>status [ <u>3]</u> | Definition  |
|--------------------------------------|-------------------------------|---|
| Objective<br>[short] data<br>sheet   | Development                   | This document contains data from<br>the objective specification for product<br>development. |
| Preliminary<br>[short] data<br>sheet | Qualification                 | This document contains data from the preliminary specification.                             |
| Product<br>[short] data<br>sheet     | Production                    | This document contains the product specification.   |

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[2] The term 'short data sheet' is explained in section "Definitions".

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#### 30 V, single N-channel Trench MOSFET

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